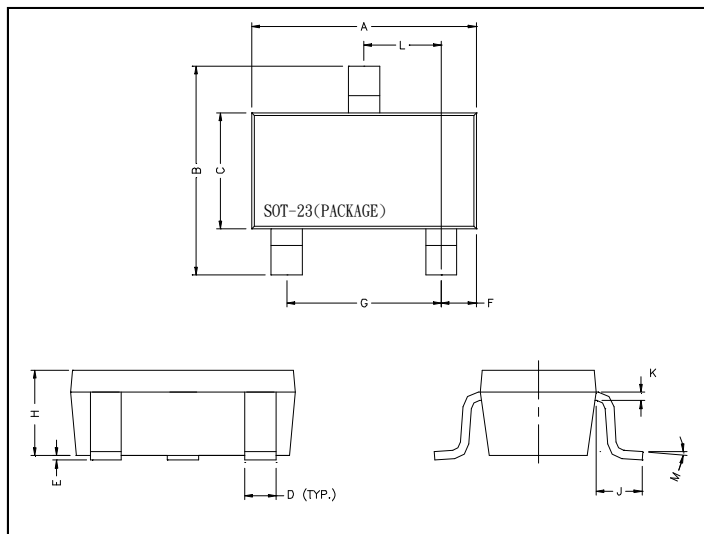


GSD882SS**NPN EPITAXIAL PLANAR TRANSISTOR****Description**

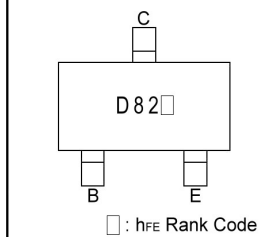
The GSD882SS is a medium power low voltage transistor, designed for audio power amplifier, DC-DC converter and voltage regulator.

Features

- High current output up to 3A
- Low saturation voltage

Package Dimensions

Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C
Collector to Base Voltage	V _{CBO}	40	V
Collector to Emitter Voltage	V _{CEO}	30	V
Emitter to Base Voltage	V _{EBO}	5	V
Collect Current(DC)	I _C	3	A
Total Power Dissipation	P _D	750	mW

Electrical Characteristics (Ta = 25°C)

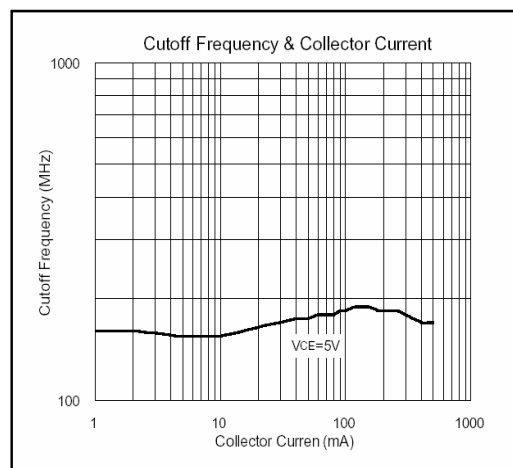
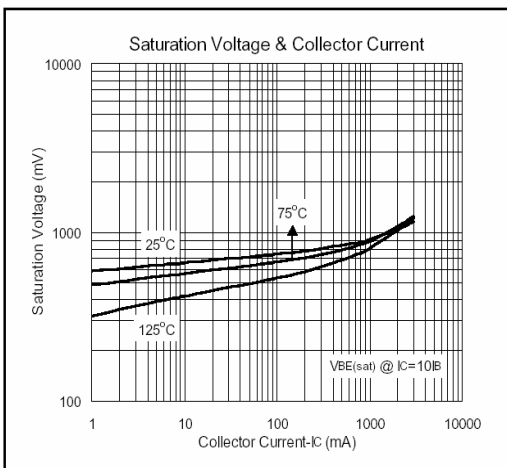
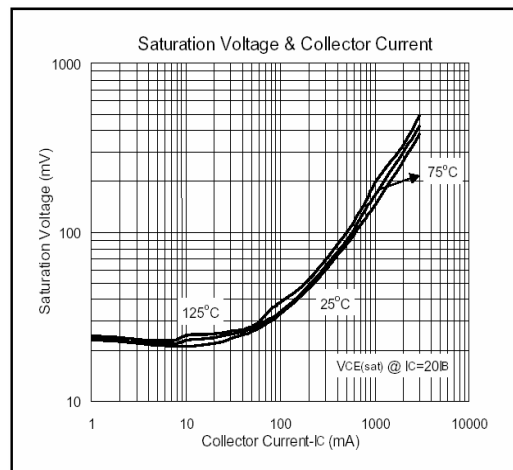
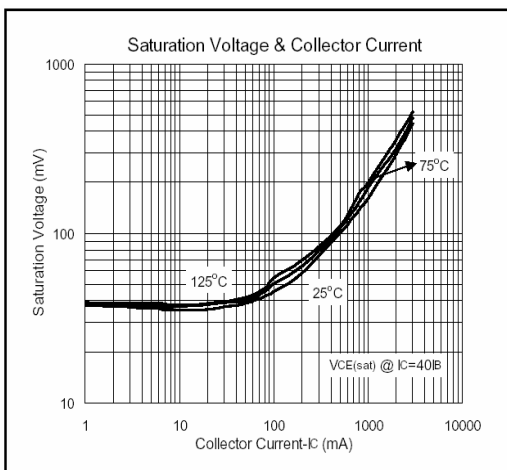
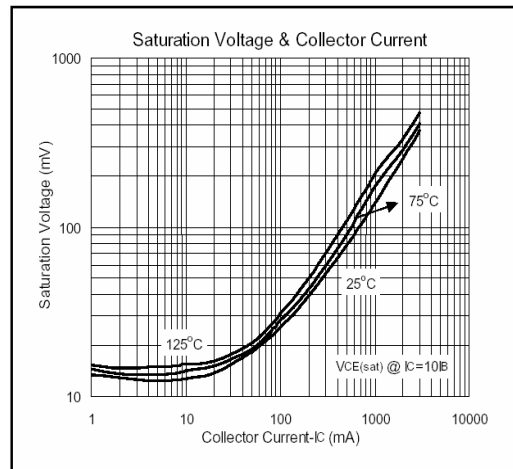
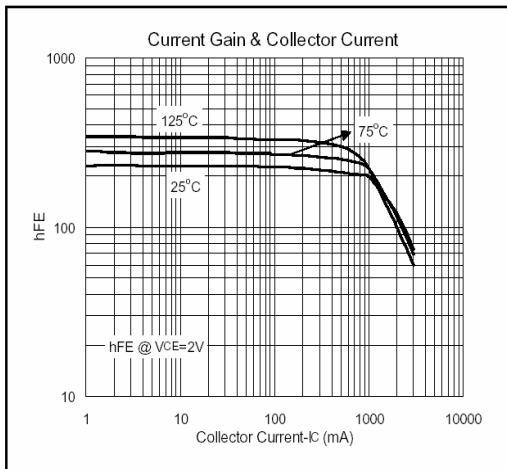
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	40	-	-	V	I _C =100uA, I _E =0
BV _{CEO}	30	-	-	V	I _C =1mA, I _B =0
BV _{EBO}	5	-	-	V	I _E =10uA, I _C =0
I _{CBO}	-	-	1	uA	V _{CB} =30V, I _E =0
I _{EBO}	-	-	1	uA	V _{EB} =3V, I _C =0
*V _{CE} (sat)	-	-	0.5	V	I _C =2A, I _B =200mA
*V _{BE} (sat)	-	-	2.0	V	I _C =2A, I _B =200mA
*h _{FE1}	30	-	-		V _{CE} =2V, I _C =20mA
*h _{FE2}	100	-	500		V _{CE} =2V, I _C =1A
f _T	-	90	-	MHz	V _{CE} =5V, I _C =100mA, f=100MHz
C _{ob}	-	45	-	pF	V _{CB} =10V, f=1MHz

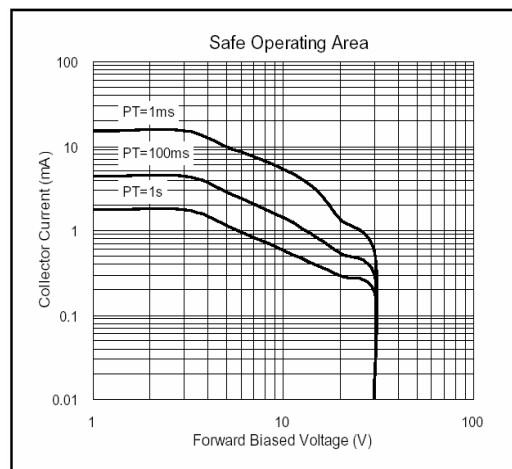
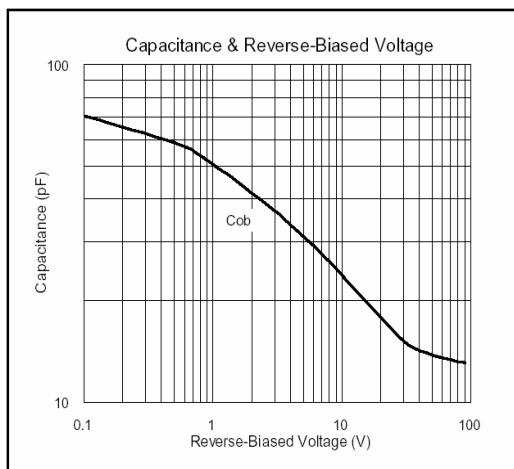
* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of hFE2

Rank	Q	P	E
Range	100 - 200	160 - 320	200 - 500

Characteristics Curve





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